

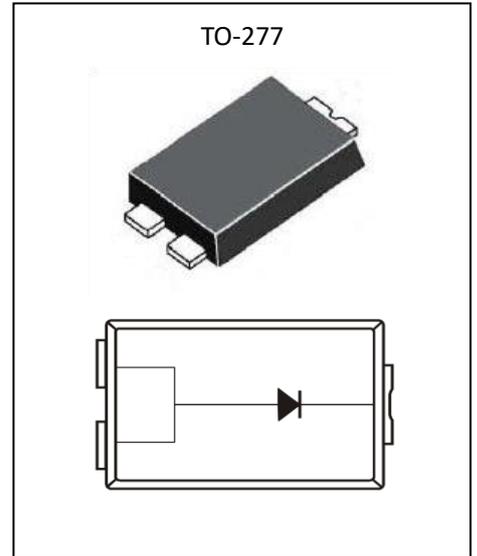


## GP10S45

### Feature

- Ultra-Low Forward Voltage
- Low Power Loss, High Efficiency
- High Current Capability
- High Surge Capability
- High Junction Temperature
- Low Reverse Current

### MARKING:



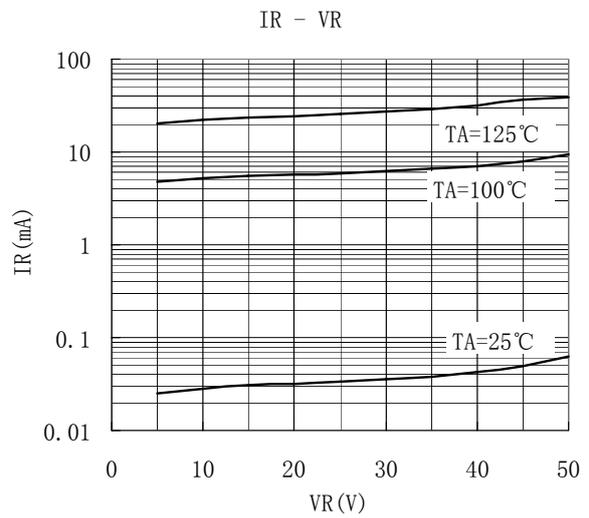
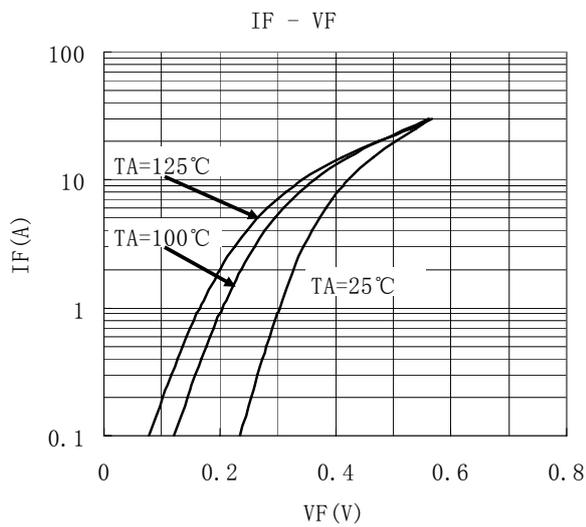
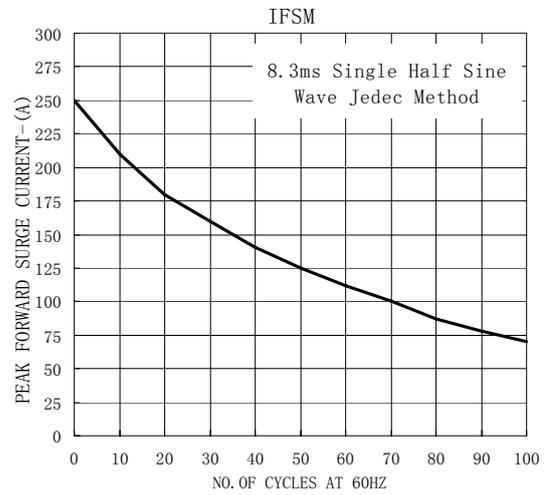
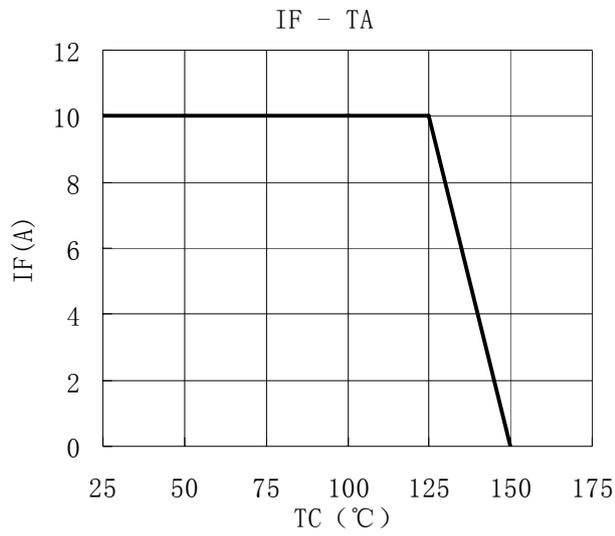
### ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Peak repetitive reverse voltage	$V_{RRM}$	45	V
Working peak reverse voltage	$V_{RWM}$		
DC blocking voltage	$V_R$		
RMS reverse voltage	$V_{R(RMS)}$	31.5	V
Average rectified output current@ $T_c=125^\circ\text{C}$	$I_o$	10	A
Non-Repetitive peak forward surge current 8.3ms half sine wave	IFSM	250	A
Thermal resistance from junction to ambient	$R_{\theta JA}$	73	$^\circ\text{C}/\text{W}$
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55~+150	$^\circ\text{C}$

### ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Reverse voltage	$V_{(BR)}$	$I_R=0.5\text{mA}$	45			V
Reverse current	$I_R$	$V_R=45\text{V}, T_J=25^\circ\text{C}$		0.06	0.12	mA
		$V_R=45\text{V}, T_J=100^\circ\text{C}$			12	
		$V_R=45\text{V}, T_J=125^\circ\text{C}$			50	
Forward voltage	$V_F$	$I_F=2\text{A}, T_J=25^\circ\text{C}$		0.33	0.38	V
		$I_F=2\text{A}, T_J=125^\circ\text{C}$		0.20		
		$I_F=10\text{A}, T_J=25^\circ\text{C}$		0.42	0.46	
		$I_F=10\text{A}, T_J=125^\circ\text{C}$		0.35		

**Typical Characteristics**



**TO-277 Package Outline Dimensions**

